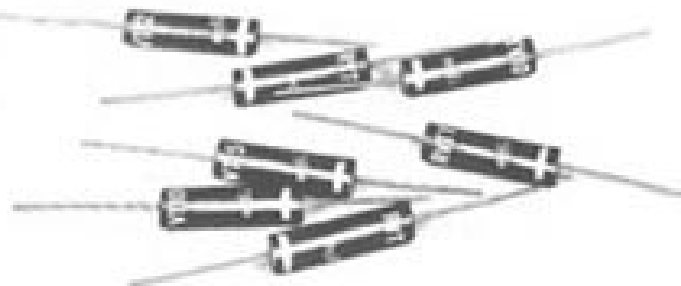




# VT RVT

## HIGH VOLTAGE 50 mA SILICON RECTIFIERS

- SMALL SIZE MOLDED PACKAGE
- PRV 10,000 TO 15,000 VOLTS
- FAST RECOVERY (R\_SERIES)
- AVALANCHE CHARACTERISTICS
- LOW LEAKAGE



EDI Type	PRV Volts	REVERSE RECOVERY TIME (Fig.4)
VT1000	10,000	-
VT1200	12,000	-
VT1500	15,000	-
RVT1000	10,000	100 ns max.
RVT1200	12,000	100 ns max.
RVT1500	15,000	100 ns max.

### ELECTRICAL CHARACTERISTICS (at $T_A=25^\circ\text{C}$ Unless Otherwise Specified)

Average Rectified Forward Current @ $50^\circ\text{C}$ , $I_o$	50 mA
Max. Peak Surge Current, $I_{FSM}$ (8.3ms)	5 Amp
Max. Forward Voltage Drop @ 50mA, $V_F$	28Volts
Max. DC Reverse Current @ PRV and $25^\circ\text{C}$ , $I_R$	1 $\mu\text{A}$
Max. DC Reverse Current @ PRV and $100^\circ\text{C}$ , $I_R$	25 $\mu\text{A}$
Ambient Operating Temperature Range, $T_A$	-55 to + $125^\circ\text{C}$
Storage Temperature Range, $T_{STG}$	-55 to + $150^\circ\text{C}$

#### NOTES:

1. It is recommended that a proper heat sink be used on the terminals of this device between the body and soldering point to prevent damage from excess heat.
2. If operated over 10,000v/inch in length, devices should be immersed in oil or re-encapsulated.

EDI reserves the right to change these specifications at any time without notice.

FIG.1

OUTPUT CURRENT vs AMBIENT TEMPERATURE

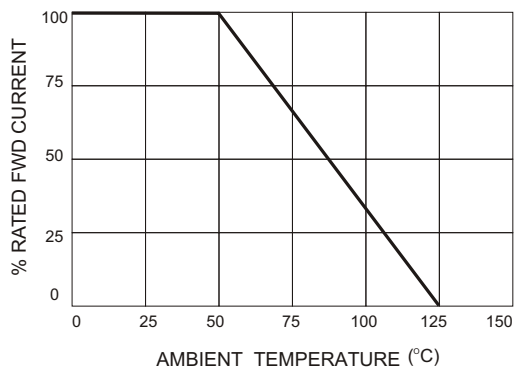


FIG.2

NON-REPETITIVE SURGE CURRENT

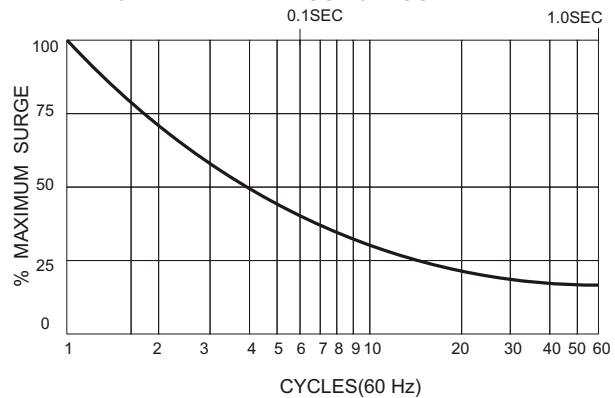


FIG.3

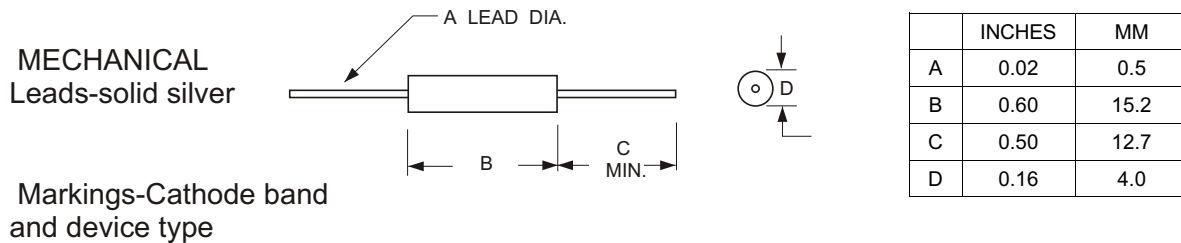
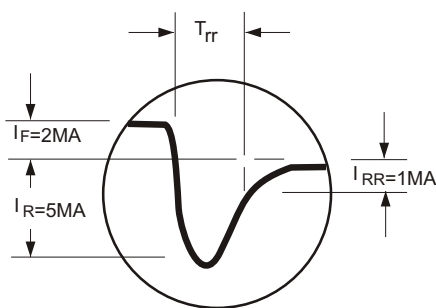


FIG.4

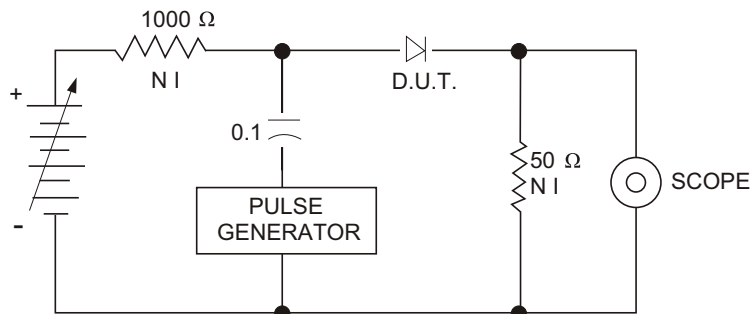
REVERSE RECOVERY TEST METHOD

RECOVERY WAVE FORM



WAVE FORMS

RECOVERY WA VE FORM



CIRCUIT

**ELECTRONIC DEVICES, INC.** DESIGNERS AND MANUFACTURERS OF SOLID STATE DEVICES SINCE 1951.

21 GRAY OAKS AVENUE \* YONKERS, NEW YORK 10710 914-965-4400 \* FAX 914-965-5531 \* 1-800-678-0828

e-mail:sales@ediodes.com \* website: <http://www.ediodes.com>